

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

# N-Channel Silicon MOSFET EFC4612R — General-Purpose Switching Device **Applications**

# **Features**

- 2.5V drive
- · Built-in gate protection resistor
- · Best suited for LiB charging and discharging switch
- · Common-drain type
- Halogen free compliance

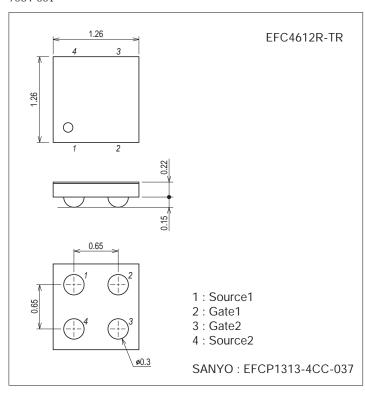
# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	VSSS		24	V
Gate-to-Source Voltage	VGSS		±12	V
Source Current (DC)	IS		6	A
Source Current (Pulse)	ISP	PW≤10μs, duty cycle≤1%	60	A
Total Dissipation	PT	When mounted on ceramic substrate (5000mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

### Package Dimensions

unit : mm (typ) 7064-001



#### **Product & Package Information** : EFCP

- Package
- JEITA, JEDEC
- Minimum Packing Quantity : 5,000 pcs./reel

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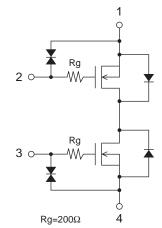
Marking

#### Taping Type : TR

0  $\cap$ 



### **Electrical Connection**



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O2412 TKIM/10511 TKIM/O0709PF TKIM TC-00001996 No. A1477-1/8

## Electrical Characteristics at Ta=25°C

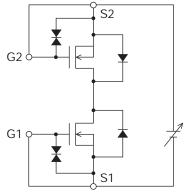
Deverse	Symbol	Conditions		Ratings			11
Parameter				min	typ	max	Unit
Source-to-Source Breakdown Voltage	V(BR)SSS	IS=1mA, VGS=0V	Test Circuit 1	24			V
Zero-Gate Voltage Source Current	ISSS	VSS=20V, VGS=0V	Test Circuit 1			1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VSS=0V	Test Circuit 2			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	VSS=10V, IS=1mA	Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	yfs	VSS=10V, IS=3A	Test Circuit 4		3.1		S
Static Source-to-Source On-State Resistance	R <sub>SS</sub> (on)1	IS=3A, VGS=4.5V	Test Circuit 5	24	39	45	mΩ
	R <sub>SS</sub> (on)2	IS=3A, VGS=4.0V	Test Circuit 5	25	41	48	mΩ
	R <sub>SS</sub> (on)3	IS=3A, VGS=3.7V	Test Circuit 5	27.5	43	50	mΩ
	RSS(on)4	IS=3A, VGS=3.1V	Test Circuit 5	31.5	48	57	mΩ
	RSS(on)5	IS=3A, VGS=2.5V	Test Circuit 5	33.5	58	72	mΩ
Turn-ON Delay Time	t <sub>d</sub> (on)		Test Circuit 7		20		ns
Rise Time	tr	Cap appaified Test Circuit			230		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.			130		ns
Fall Time	tf	1			210		ns
Total Gate Charge	Qg	V <sub>SS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =6A			7		nC
Forward Source-to-Source Voltage	VF(S-S)	IS=3A, VGS=0V	Test Circuit 6		0.8	1.2	V

# **Ordering Information**

Device Package		Shipping	memo	
EFC4612R-TR	EFCP	5,000pcs./reel	Pb Free and Halogen Free	

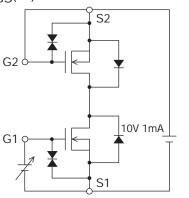
Test circuits are example of measuring FET1 side Test Circuit 1





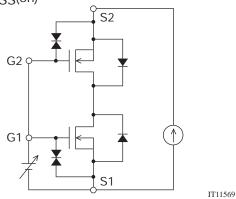


Test Circuit 3 V<sub>GS</sub>(off)

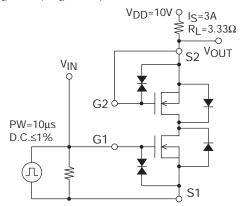


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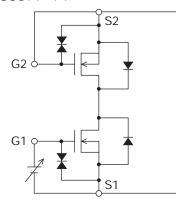
Test Circuit 5 RSS(on)



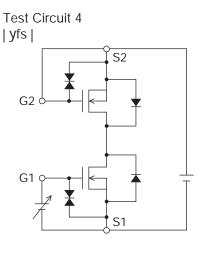
Test Circuit 7 t<sub>d</sub>(on), t<sub>r</sub>, t<sub>d</sub>(off), t<sub>f</sub>



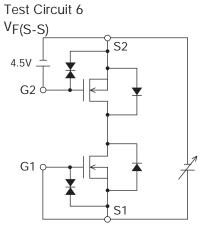




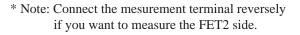
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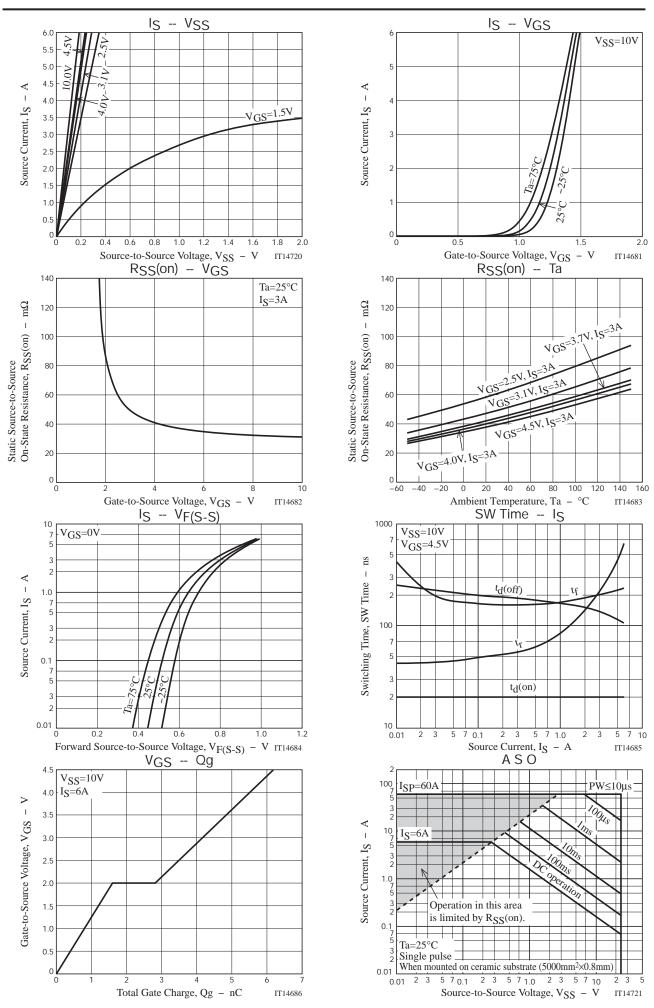


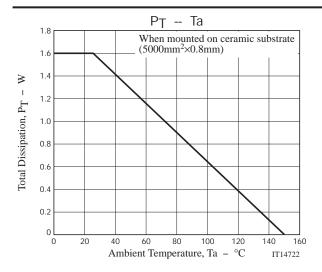
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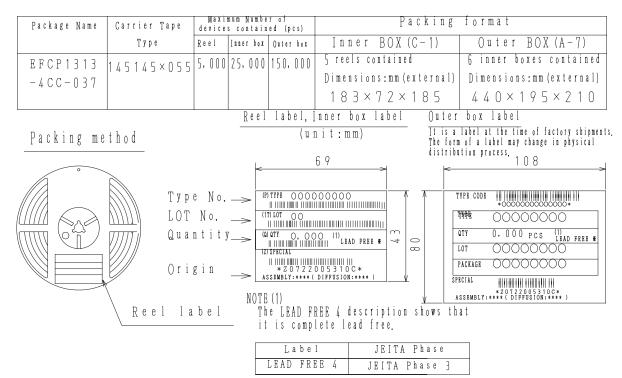






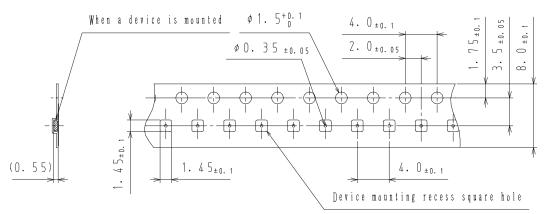
### Taping Specification EFC4612R-TR

1. Packing Format

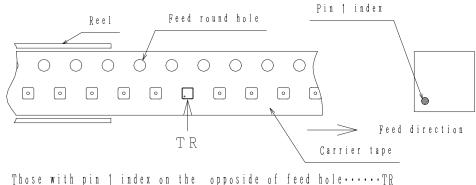


## 2. Taping configuration

2-1. Carrier tape size (unit:mm)



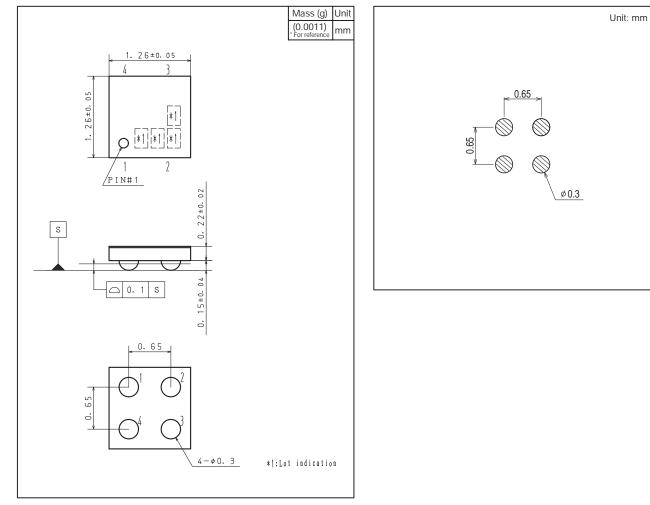
2-2. Device placement direction



No. A1477-6/8

Land Pattern Example

# Outline Drawing EFC4612R-TR



Note on usage : Since the EFC4612R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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